Octal 3-State Non-Inverting Transparent Latch

High-Performance Silicon-Gate CMOS

The MC74HC373A is identical in pinout to the LS373. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

These latches appear transparent to data (i.e., the outputs change asynchronously) when Latch Enable is high. When Latch Enable goes low, data meeting the setup and hold time becomes latched.

The Output Enable input does not affect the state of the latches, but when Output Enable is high, all device outputs are forced to the high-impedance state. Thus, data may be latched even when the outputs are not enabled.

The HC373A is identical in function to the HC573A which has the data inputs on the opposite side of the package from the outputs to facilitate PC board layout.

The HC373A is the non-inverting version of the HC533A.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7.0 A Requirements
- Chip Complexity: 186 FETs or 46.5 Equivalent Gates
- Pb-Free Packages are Available*



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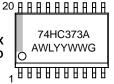
MARKING DIAGRAMS



PDIP-20 N SUFFIX CASE 738 ²⁰AAAAAAAAAAA MC74HC373AN O AWLYYWWG VVVVVVVVVVVVV

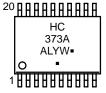


SOIC-20 DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E





A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G = Pb-Free Package
Pb-Free Package

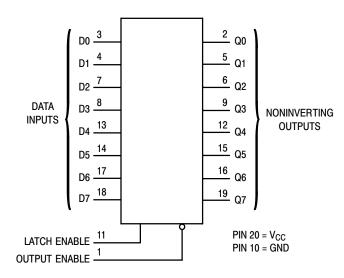
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

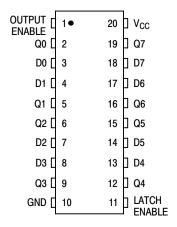
LOGIC DIAGRAM



Design Criteria	Value	Units
Internal Gate Count*	46.5	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	0.0075	рJ

^{*}Equivalent to a two-input NAND gate.

PIN ASSIGNMENT



FUNCTION TABLE

	Output						
Output Enable	Latch Enable	D	Q				
L	Н	Н	Н				
L	Н	L	L				
L	L	Χ	No Change				
н	Х	Х	Z				

X = Don't CareZ = High Impedance

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 35	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC, SSOP or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)			6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND	0)	0	V_{CC}	V
T _A	Operating Temperature, All Package Types		- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 2.0$ (Figure 1) $V_{CC} = 4.5$ $V_{CC} = 6.0$	V	0 0 0	1000 500 400	ns

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC373AN	PDIP-20	18 Units / Box
MC74HC373ANG	PDIP-20 (Pb-Free)	18 Units / Box
MC74HC373ADW	SOIC-20 WIDE	38 Units / Rail
MC74HC373ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HC373ADWR2	SOIC-20 WIDE	1000 Units / Reel
MC74HC373ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Units / Reel
MC74HC373ADT	TSSOP-20*	75 Units / Rail
MC74HC373ADTG	TSSOP-20*	75 Units / Rail
MC74HC373ADTR2	TSSOP-20*	2500 Units / Reel
MC74HC373ADTR2G	TSSOP-20*	2500 Units / Reel
MC74HC373AF	SOEIAJ-20	40 Units / Rail
MC74HC373AFG	SOEIAJ-20 (Pb-Free)	40 Units / Rail
MC74HC373AFEL	SOEIAJ-20	2000 Units / Reel
MC74HC373AFELG	SOEIAJ-20 (Pb-Free)	2000 Units / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guar	anteed Lim	it	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
			2.0	1.5	1.5	1.5	V
V_{IH}	Minimum High-Level Input Voltage	$V_{\text{out}} = V_{\text{CC}} - 0.1 \text{ V}$ $ I_{\text{out}} \le 20 \mu\text{A}$	3.0	2.1	2.1	2.1	V
	Voltage	Poutl ≤ 20 μA	4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
\ /	Maniarum Laur Laur Laur	V 04.V					V
V_{IL}	Maximum Low–Level Input	V _{out} = 0.1 V	2.0	0.5	0.5	0.5	V
	Voltage	$ I_{out} \le 20 \mu A$	3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V _{OH}	Minimum High-Level Output	$V_{in} = V_{IH}$	2.0	1.9	1.9	1.9	V
	Voltage	$ I_{out} \leq 20 \mu A$	4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		$V_{in} = V_{IH}$ $ I_{out} \le 2.4 \text{ mA}$	3.0	2.48	2.34	2.2	
		$ I_{out} \leq 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	
		$ I_{out} \le 7.8 \text{ mA}$	6.0	5.48	5.34	5.2	
V _{OL}	Maximum Low-Level Output	$V_{in} = V_{IL}$	2.0	0.1	0.1	0.1	V
02	Voltage	$ I_{\text{out}} \leq 20 \mu\text{A}$	4.5	0.1	0.1	0.1	
		1 33.1	6.0	0.1	0.1	0.1	
		$V_{in} = V_{IL}$ $ I_{out} \le 2.4 \text{ mA}$	3.0	0.26	0.33	0.4	
		$ I_{out} \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
		$ I_{out} \le 7.8 \text{ mA}$	6.0	0.26	0.33	0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
loz	Maximum Three-State	Output in High-Impedance State	6.0	± 0.5	± 5.0	± 10	μΑ
	Leakage Current	$V_{in} = V_{IL}$ or V_{IH}					
		$V_{out} = V_{CC}$ or GND					
I _{CC}	Maximum Quiescent Supply	V _{in} = V _{CC} or GND	6.0	4.0	40	160	μΑ
	Current (per Package)	I _{out} = 0 μA					

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D). **AC ELECTRICAL CHARACTERISTICS** ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6.0 \text{ ns}$)

		V _{CC}	Guaranteed Limit		it	
Symbol	Parameter	v	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PLH}	Maximum Propagation Delay, Input D to Q	2.0	125	155	190	ns
t _{PHL}	(Figures 1 and 5)	3.0	80	110	130	
		4.5	25	31	38	
		6.0	21	26	32	
t _{PLH}	Maximum Propagation Delay, Latch Enable to Q	2.0	140	175	210	ns
t _{PHL}	(Figures 2 and 5)	3.0	90	120	140	
		4.5	28	35	42	
		6.0	24	30	36	
t _{PLZ}	Maximum Propagation Delay, Output Enable to Q	2.0	150	190	225	ns
t _{PHZ}	(Figures 3 and 6)	3.0	100	125	150	
		4.5	30	38	45	
		6.0	26	33	38	
t _{PZL}	Maximum Propagation Delay, Output Enable to Q	2.0	150	190	225	ns
t _{PZH}	(Figures 3 and 6)	3.0	100	125	150	
		4.5	30	38	45	
		6.0	26	33	38	
t _{TLH}	Maximum Output Transition Time, Any Output	2.0	60	75	90	ns
t _{THL}	(Figures 1 and 5)	3.0	23	27	32	
		4.5	12	15	18	
		6.0	10	13	15	
C _{in}	Maximum Input Capacitance		10	10	10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State)		15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

			•	Ty	pical @ 25°C, V _{CC} = 5.0 V	
C_PD	Power Dissipation	Capacitance (Per Enable	d Output)*		36	pF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6.0 \text{ ns}$)

				Guaranteed Limit						
			v _{cc}	– 55 to	25°C	≤ 8	5°C	≤ 12	25°C	
Symbol	Parameter	Figure	Volts	Min	Max	Min	Max	Min	Max	Unit
t _{su}	Minimum Setup Time, Input D to Latch Enable	4	2.0 3.0 4.5 6.0	25 20 5.0 5.0		30 25 6.0 6.0		40 30 8.0 7.0		ns
t _h	Minimum Hold Time, Latch Enable to Input D	4	2.0 3.0 4.5 6.0	5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		ns
t _w	Minimum Pulse Width, Latch Enable	2	2.0 3.0 4.5 6.0	60 23 12 10		75 27 15 13		90 32 18 15		ns
t _r , t _f	Maximum Input Rise and Fall Times	1	2.0 3.0 4.5 6.0		1000 800 500 400		1000 800 500 400		1000 800 500 400	ns

SWITCHING WAVEFORMS

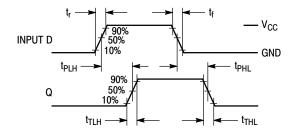


Figure 1.

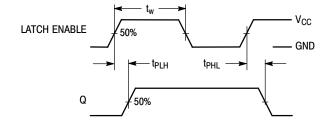


Figure 2.

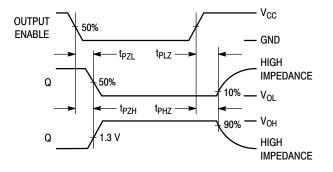


Figure 3.

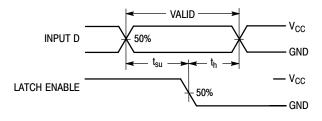
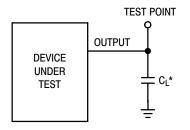
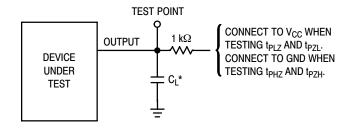


Figure 4.

TEST CIRCUITS





*Includes all probe and jig capacitance

Figure 5.

Figure 6.

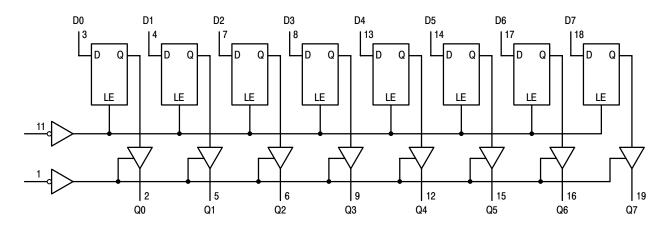
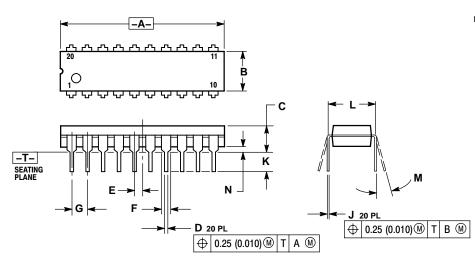


Figure 7. EXPANDED LOGIC DIAGRAM

^{*}Includes all probe and jig capacitance

PACKAGE DIMENSIONS

PDIP-20 **N SUFFIX** PLASTIC DIP PACKAGE CASE 738-03 ISSUE E



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

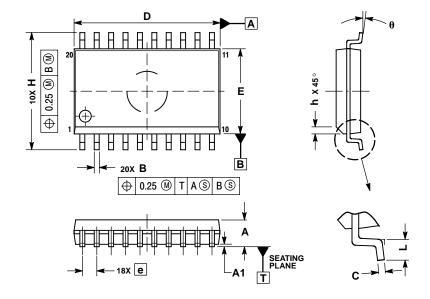
 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

- DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	1.010	1.070	25.66	27.17
В	0.240	0.260	6.10	6.60
С	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050	BSC	1.27	BSC
F	0.050	0.070	1.27	1.77
G	0.100	0.100 BSC		BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300	BSC	7.62	BSC
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G**

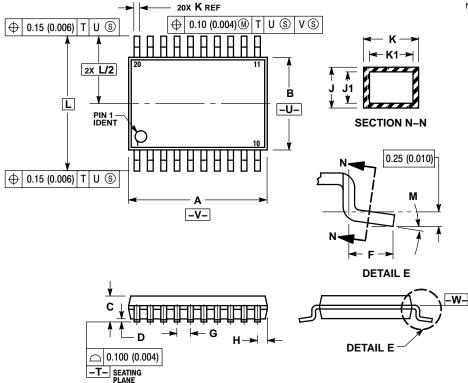


- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION, ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS					
DIM	MIN	MAX				
Α	2.35	2.65				
A1	0.10	0.25				
В	0.35	0.49				
С	0.23	0.32				
D	12.65	12.95				
E	7.40	7.60				
е	1.27	BSC				
Н	10.05	10.55				
h	0.25	0.75				
L	0.50	0.90				
θ	0 °	7 °				

PACKAGE DIMENSIONS

TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:

 - MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 - SIDE.

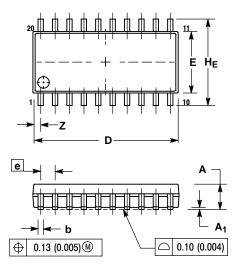
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER CIDE.
 - SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

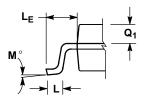
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 - 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 - 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.27	0.37	0.011	0.015
L	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252 BSC	
M	0°	8°	0°	8°

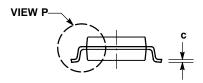
PACKAGE DIMENSIONS

SOEIAJ-20 **F SUFFIX** CASE 967-01 **ISSUE O**





DETAIL P



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI

- ILES:
 DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.
 OINTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD
 FLASH OR PROTRUSIONS AND ARE MEASURED
 AT THE PARTING LINE. MOLD FLASH OR
 PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
 PER SIDE.
 TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT
 INCLUDE DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
 TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 DAMBAR CANNOT BE LOCATED ON THE LOWER
 RADIUS OR THE FOOT. MINIMUM SPACE
 BETWEEN PROTRUSIONS AND ADJACENT LEAD
 TO BE 0.46 (0.018). TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10 °
Qı	0.70	0.90	0.028	0.035
Z		0.81		0.032

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